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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/075,464	02/15/2002	Shigeru Kawanaka	219713US2	7542	
22850 759	90 07/01/2004		EXAMINER		
OBLON, SPIVAK, MCCLELLAND, MAIER & NEUSTADT, P.C.			QUINTO, KEVIN V		
1940 DUKE STREET ALEXANDRIA, VA 22314			ART UNIT	PAPER NUMBER	
	, · ·		2826		

DATE MAILED: 07/01/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
		10/075,464	KAWANAKA, SH	AWANAKA, SHIGERU		
	Office Action Summary	Examiner	Art Unit	- (X		
		Kevin Quinto	2826			
Period f	Th MAILING DATE of this communication ap or Reply	op ars on the cov r sh t with th	ne correspond nc ad	ddress		
THE - Extended - aftended - if thended - from Fail - Any	HORTENED STATUTORY PERIOD FOR REPI MAILING DATE OF THIS COMMUNICATION ensions of time may be available under the provisions of 37 CFR 1. r SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a rej O period for reply is specified above, the maximum statutory period ure to reply within the set or extended period for reply will, by status reply received by the Office later than three months after the mailined patent term adjustment. See 37 CFR 1.704(b).	.136(a). In no event, however, may a reply b ply within the statutory minimum of thirty (30) I will apply and will expire SIX (6) MONTHS I te, cause the application to become ABANDO	e timely filed days will be considered time from the mailing date of this of DNED (35 U.S.C. § 133).			
Status						
1)[🛛	Responsive to communication(s) filed on 08 /	<u> April 2004</u> .				
2a)□		is action is non-final.				
3)□	Since this application is in condition for allowa		prosecution as to the	e merits is		
•	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposit	tion of Claims					
4)⊠	Claim(s) 3-12 and 15-20 is/are pending in the	e application.				
,	4a) Of the above claim(s) <u>16-20</u> is/are withdrawn from consideration.					
5)🖂						
6)🖂						
7)	Claim(s) is/are objected to.					
8)□	Claim(s) are subject to restriction and/	or election requirement.				
Applicat	ion Papers					
9)[The specification is objected to by the Examin	er.				
-	0)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.					
,—	Applicant may not request that any objection to the					
	Replacement drawing sheet(s) including the correct	- · · ·	, ,	FR 1 121(d)		
11)	The oath or declaration is objected to by the E		=	, ,		
	under 35 U.S.C. § 119			. •		
	•					
	Acknowledgment is made of a claim for foreig	n phonty under 35 U.S.C. § 119	(a)-(d) or (f).			
a)	a) All b) Some * c) None of:					
	1. Certified copies of the priority documen					
	2. Certified copies of the priority documen	• •				
	3. Copies of the certified copies of the price		eived in this National	Stage		
* (application from the International Burea		•			
`	See the attached detailed Office action for a lis	t of the certified copies not rece	ervea.			
Attachmen	• •		(DT-			
	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948)	4) ∐ Interview Summ Paper No(s)/Mai				
3) 🔲 Infor	mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08	——————————————————————————————————————	al Patent Application (PT	O-152)		
Pape	er No(s)/Mail Date	6) 🔲 Other:				

Application/Control Number: 10/075,464 Page 2

Art Unit: 2826

DETAILED ACTION

Response to Arguments

1. Applicant's arguments with respect to claim 8 have been considered but are moot in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Parris et al. (USPN 5,604,700) in view of Venkatasen et al. (USPN 5,736,435) and further in view of Yu (USPN 6,534,373 B1).
- 4. In reference to claim 8, Parris et al. (USPN 5,604,700, hereinafter referred to as the "Parris" reference) discloses a similar device. Figures 1, 4, and 5 illustrate a semiconductor memory device with a memory cell formed of two transistors on a semiconductor layer. The first and second memory transistors are connected in series with a common wordline. It is understood that one side is connected to a bitline and the other side is supplied with a reference potential. Parris does not disclose forming the transistors on an SOI substrate (a semiconductor layer formed on an insulating film). However the use of an SOI substrate is well known in the art. Venkatasen et al. (USPN

Art Unit: 2826

5,736,435, hereinafter referred to as the "Venkatasen" reference) discloses that transistors formed on SOI substrates have the advantage of better performance at lower operating voltages than those formed on bulk substrates (column 1, lines 30-38). In view of Venkatasen, it would therefore be obvious to implement the device of Parris onto an SOI substrate. Neither Parris nor Venkatasen discloses implementing partially depleted transistors in the memory cell. However, the use of partially depleted transistors is well known in the art. Yu (USPN 6,534,373 B1) discloses that implementing a partially depleted transistor (such as the device of figure 1) provides the advantages of reduced source-drain junction capacitance and is latch-up free (column 2, lines 1-4). It would therefore be obvious to implement the partially depleted transistors in the memory cell.

Allowable Subject Matter

- 5. Claims 3-7, 9-12, and 15 are allowed.
- 6. The following is a statement of reasons for the indication of allowable subject matter: the examiner is unaware of any prior art which suggests using the exact series circuit having partially depleted transistors as described by the applicant.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kevin Quinto whose telephone number is (571) 272-1920. The examiner can normally be reached on M-F 8AM-5PM.

Application/Control Number: 10/075,464 Page 4

Art Unit: 2826

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KVQ

Minhloan Tran Primary Examiner Art Unit 2826

hom Tom